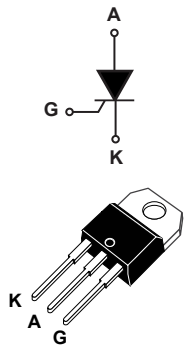
16 A 800 V high temperature SCR thyristor in TO-220AB insulated package



TO-220AB insulated

Features

- High junction temperature: $T_j$max. = 150 °C
- V_{DRM} / V_{RRM} = 800 V
- V_{DSM} / V_{RSM} = 900 V
- Tight I_{GT} spread: 5 to 8 mA
- High static immunity dV/dt = 500 V/µs at 150 °C
- High turn-on rise dI/dt at 100 A/µs
- Halogen-free molding, lead-free plating
- Insulated package TO-220AB:
  - Insulated voltage: 2500 V_{RMS}
  - Complies with UL 1557 (File ref : E81734)
- ECOPACK2 compliant

Applications

- Inrush current limiting circuits in AC/DC converters
- General purpose AC line load switching
- Heating resistor control, solid state relays
- Crowbar and power bus discharge circuits

Product status
TN1605H-8I

Product summary	
Order code	TN1605H-8I
Package	TO-220AB ins.
$I_{T(RMS)}$	16 A
V_{DRM}/V_{RRM}	800 V
T_j max.	150 °C

Description

Thanks to its operating junction temperature up to 150°C, the TN1605H-8I offers high thermal performance operation up to 16 A rms in a TO-220AB insulated package.

Its trade-off noise immunity (dV/dt = 500 V/µs) versus its gate triggering current (maximum I_{GT} = 8 mA) and its turn-on current rise (dI/dt = 100 A/µs) allows to design robust and compact control circuit in AC/DC converters for inrush current limiting circuits and industrial drives, such as overvoltage crowbar protection, motor control circuits and power tools.

1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	T_C = 118 °C	16	A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)	T_C = 118 °C	10	A
		T_C = 127 °C	8	
		T_C = 135 °C	6	
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25 °C)	t_P = 8.3 ms	177	A
		t_P = 10 ms	160	
I^2t	I^2t value for fusing	t_P = 10 ms	128	A²s
V_{DRM}, V_{RRM}	Repetitive peak off-state voltage		800	V
V_{DSM}, V_{RSM}	Non repetitive peak off-state voltage	t_P = 10 ms	V_{DRM} / V_{RRM} + 100 V	V
dI/dt	Critical rate of rise of on-state current I_G = 2 x I_{GT}, t_r < 100 ns	f = 60 Hz	100	A/µs
I_{GM}	Peak gate current (t_p = 20 µs)	T_j = 150 °C	4	A
$P_{G(AV)}$	Average peak gate power dissipation	T_j = 150 °C	1	W
V_{RGM}	Maximum peak reverse gate voltage		5	V
T_{stg}	Storage junction temperature range		-40 to +150	°C
T_j	Operating junction temperature range		-40 to +150	
T_l	Maximum lead temperature soldering during 10 s		260	
V_{ins}	RMS insulation voltage during 1 min.		2500	V

Table 2. Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test conditions			Value	Unit
I_{GT}	V_D = 12 V, R_L = 33 Ω		Min.	5	mA
			Max.	8	
V_{GT}				1.3	V
V_{GD}	V_D = V_{DRM}, R_L = 3.3 kΩ	T_j = 150 °C	Min.	0.2	V
I_H	I_T = 500 mA, gate open		Max.	30	mA
I_L	I_G = 1.2 x I_{GT} max.		Max.	40	mA
dV/dt	V_{OUT} = 536 V, gate open	T_j = 150 °C	Min.	500	V/µs
t_{gt}	I_T = 32 A, V_D = 536 V, I_G = 12 mA, (dI_G/dt) max = 0.2 A/µs		Typ.	1.9	µs
t_q	I_T = 32 A, V_D = 536 V, V_R = 25 V, dV_D/dt = 40 V/µs	T_j = 25 °C	Typ.	25	µs
		T_j = 150 °C	Typ.	85	µs

Table 3. Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	I_{TM} = 32 A, t_p = 380 µs	T_j = 25 °C	Max.	1.55	V
V_{TO}	Threshold voltage	T_j = 150 °C	Max.	0.82	
R_D	Dynamic resistance	T_j = 150 °C	Max.	25	mΩ
I_{DRM}, I_{RRM}	V_D = V_{DRM} ; V_R = V_{RRM}	T_j = 25 °C	Max.	1	µA
		T_j = 150 °C		3.5	mA

Table 4. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	Max.	2.2	°C/W
$R_{th(j-a)}$	Junction to ambient	Typ.	60	

1.1 Characteristics curves

Figure 1. Maximum average power dissipation versus average on-state current

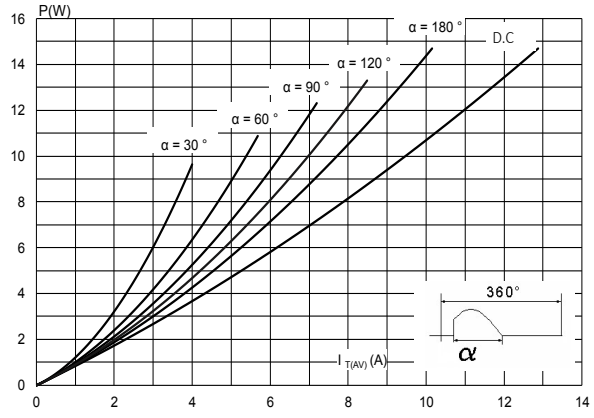


Figure 2. Average and DC on-state current versus case temperature

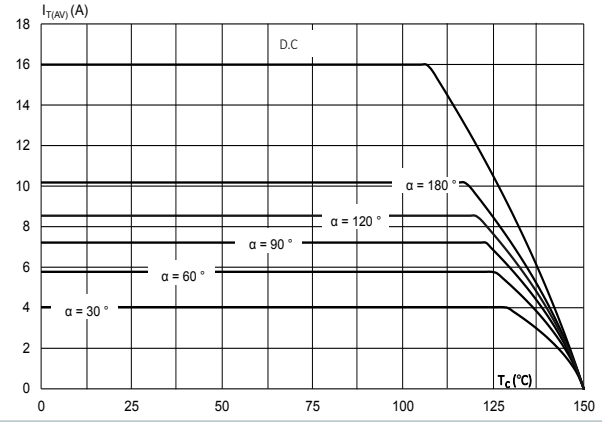


Figure 3. Average and D.C. on-state current versus ambient temperature

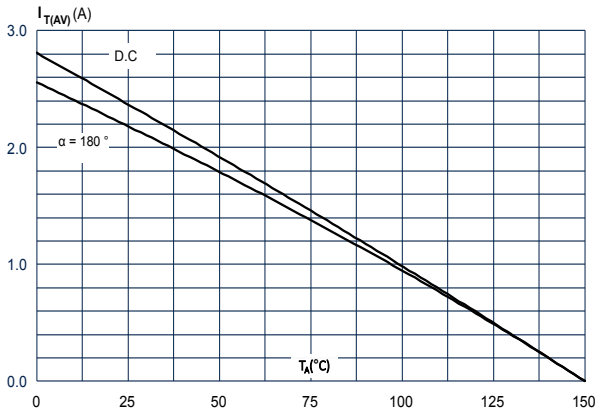


Figure 4. On-state characteristics (maximum values)

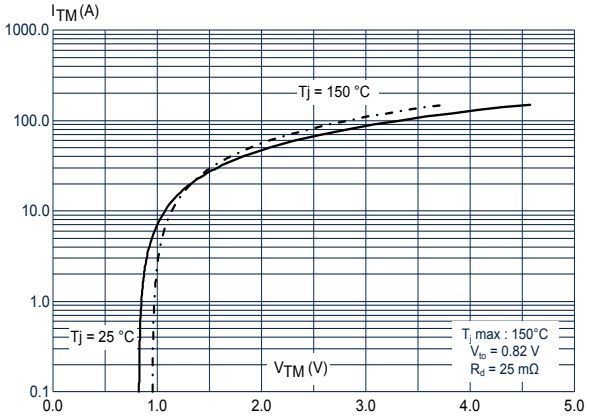


Figure 5. Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration

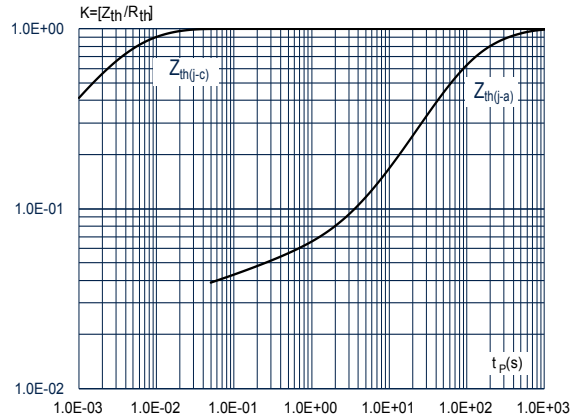


Figure 6. Surge peak on-state current versus number of cycles

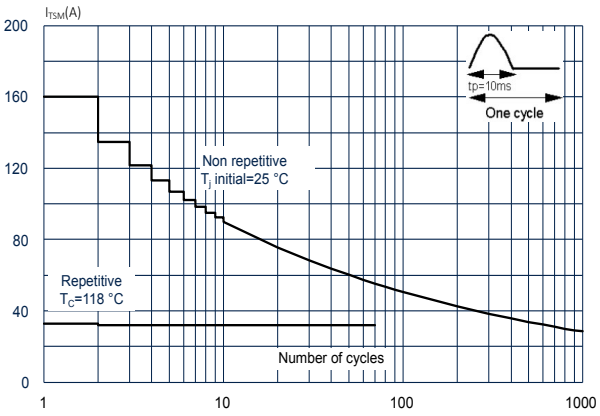


Figure 7. Non repetitive surge peak on-state current for a sinusoidal pulse with width t_p < 10 ms

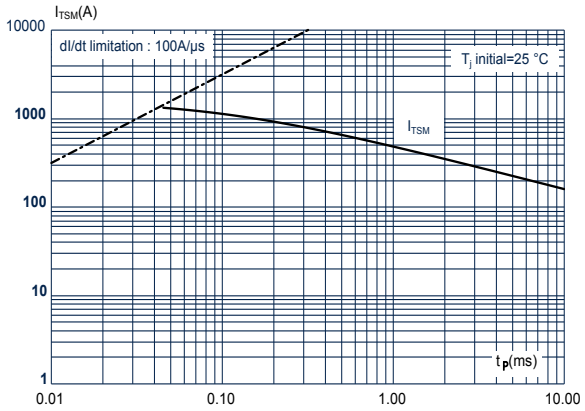


Figure 8. Relative variation of holding current and latching current versus junction temperature (typical values)

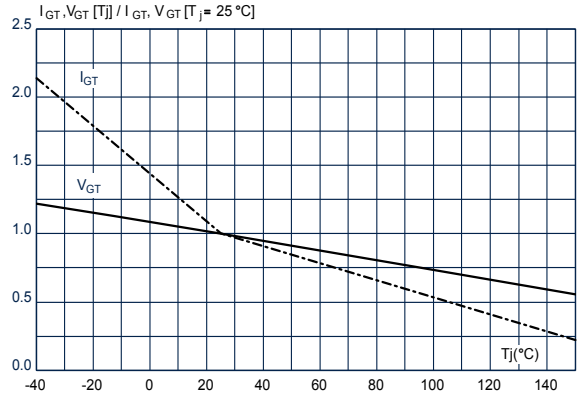


Figure 9. Relative variation of gate triggering current and voltage versus junction temperature (typical values)

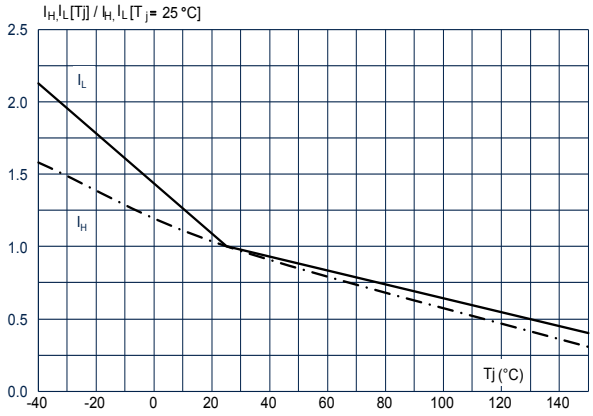


Figure 10. Relative variation of static dV/dt immunity versus junction temperature (typical values)

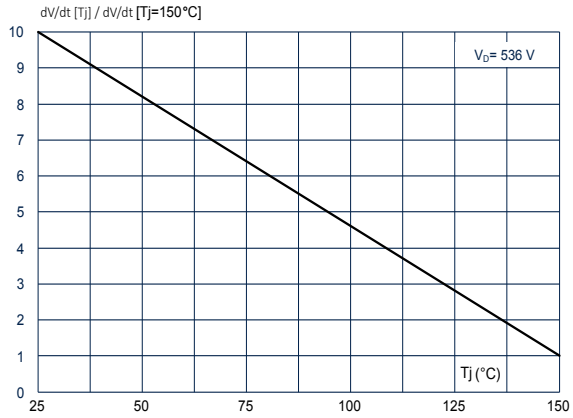
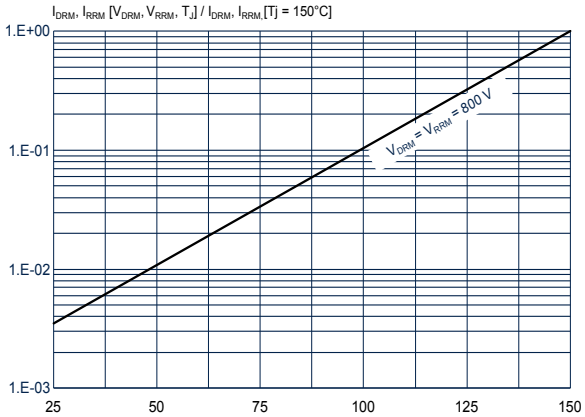


Figure 11. Relative variation of leakage current versus junction temperature for 800 V blocking voltage



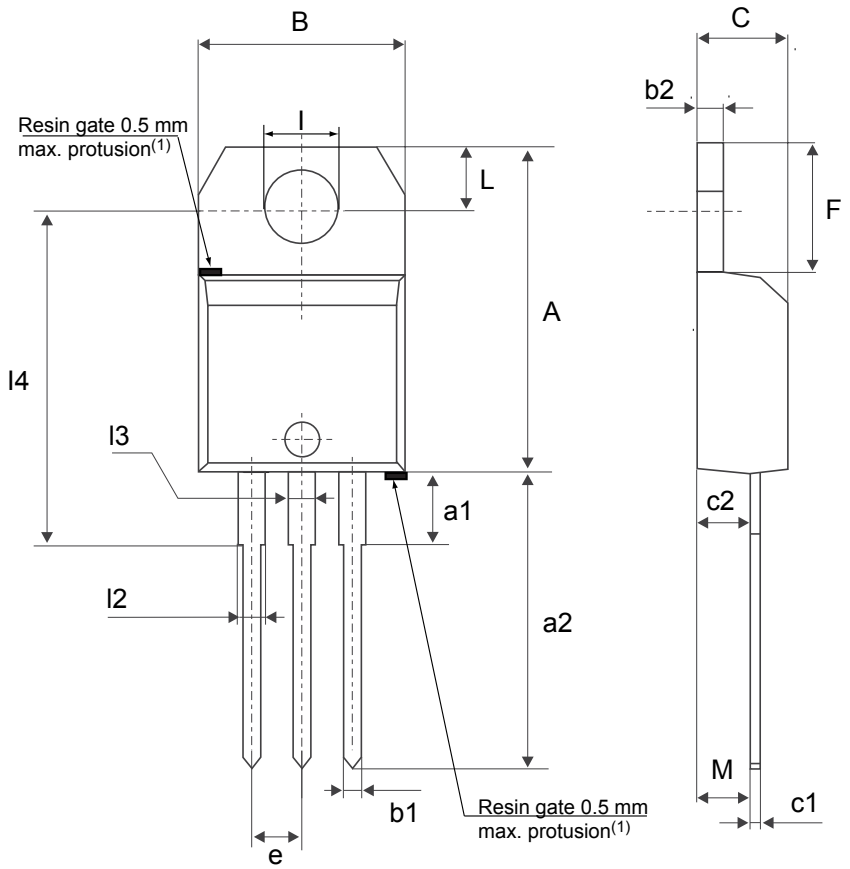
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 TO-220AB insulated package information

- Molding compound resin is halogen-free and meets flammability standard UL94 level 0
- Lead-free package leads finishing
- ECOPACK2 compliant
- Recommended torque: 0.4 to 0.6 N.m

Figure 12. TO-220AB insulated package outline



(1)Resin gate position accepted in one of the two positions or in the symmetrical opposites.

Table 5. TO-220AB insulated package mechanical data

Ref.	Dimensions					
	Millimeters			Inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
B	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
C	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
e	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
I	3.73		3.88	0.1469		0.1528
L	2.65		2.95	0.1043		0.1161
l2	1.14		1.70	0.0449		0.0669
l3	1.14		1.70	0.0449		0.0669
l4	15.80	16.40	16.80	0.6220	0.6457	0.6614
M		2.6			0.1024	

1. *Inch dimensions are for reference only.*

3 Ordering information

Figure 13. **Ordering information scheme**

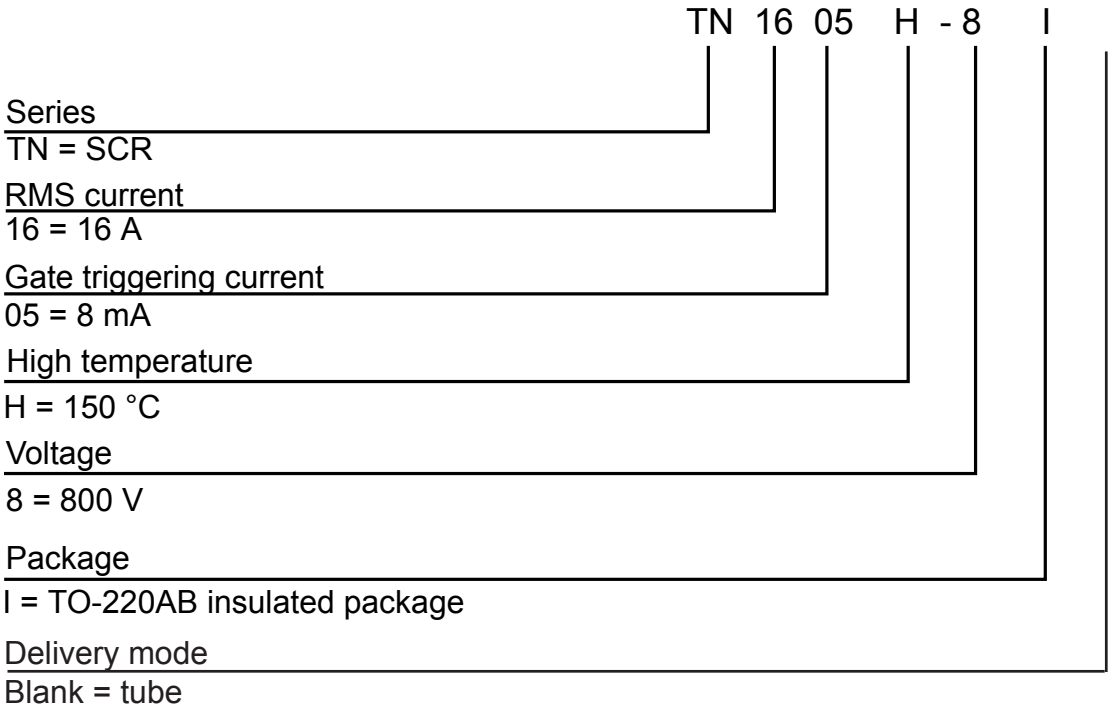


Table 6. **Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN1605H-8I	TN1605H8I	TO-220AB ins.	2.3 g	50	Tube

Revision history

Table 7. **Document revision history**

Date	Revision	Changes
05-Dec-2022	1	Initial release.

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